

### FEATURES

- Double Side Cooling
- High Surge Capability

### APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages $V_{DRM}$ and $V_{RRM}$ V	Conditions
DCR2720V52* DCR2720V50 DCR2720V48	5200 5000 4800	$T_{vj} = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$ , $I_{DRM} = I_{RRM} = 200\text{mA}$ , $V_{DRM}, V_{RRM} t_p = 10\text{ms}$ , $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively

Lower voltage grades available.

\* 5000V @  $-40^{\circ}\text{C}$ , 5200V @  $0^{\circ}\text{C}$

### ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR2720V52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### KEY PARAMETERS

$V_{DRM}$	5200V
$I_{T(AV)}$	2720A
$I_{TSM}$	36700A
$dV/dt^*$	1500V/ $\mu\text{s}$
$dI/dt$	300A/ $\mu\text{s}$

\* Higher  $dV/dt$  selections available

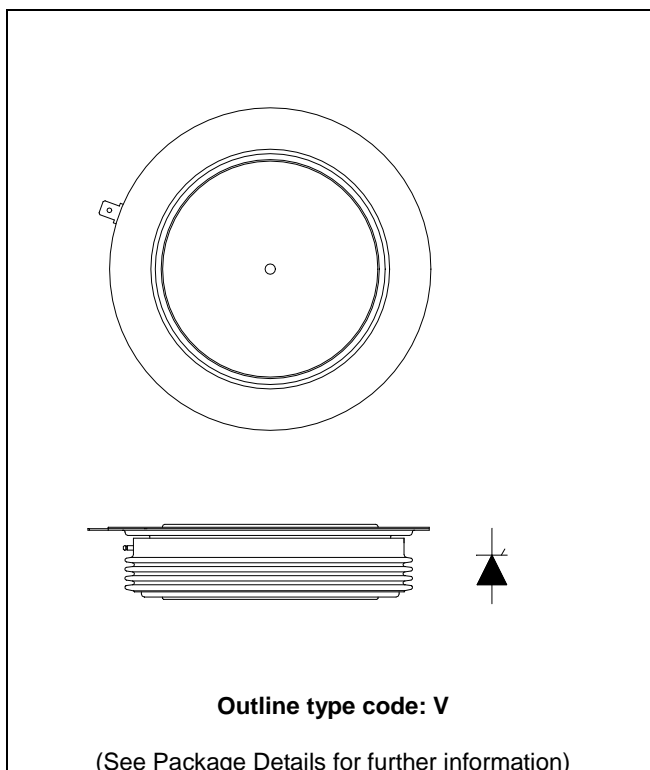


Fig. 1 Package outline

## CURRENT RATINGS

$T_{case} = 60^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
<b>Double Side Cooled</b>				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	2720	A
$I_{T(RMS)}$	RMS value	-	4270	A
$I_T$	Continuous (direct) on-state current	-	4120	A

## SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
$I_{TSM}$	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$	36.7	kA
$I^2t$	$I^2t$ for fusing	$V_R = 0$	6.73	$\text{MA}^2\text{s}$

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.00746	°C/W
		Single side cooled	Anode DC	-	0.0130	°C/W
			Cathode DC	-	0.0178	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 54kN	Double side	-	0.002	°C/W
		(with mounting compound)	Single side	-	0.004	°C/W
T <sub>vj</sub>	Virtual junction temperature	Blocking V <sub>DRM</sub> / V <sub>RRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			48.0	59.0	kN

## DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	200	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, gate open		-	1500	V/μs
dI/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	150	A/μs
		Gate source 30V, 10Ω, t <sub>r</sub> < 0.5μs, T <sub>j</sub> = 125°C	Non-repetitive	-	300	A/μs
V <sub>T(TO)</sub>	Threshold voltage – Low level	500A to 2000A at T <sub>case</sub> = 125°C		-	0.90	V
	Threshold voltage – High level	2000A to 7200A at T <sub>case</sub> = 125°C		-	1.1	V
r <sub>T</sub>	On-state slope resistance – Low level	500A to 2000A at T <sub>case</sub> = 125°C		-	0.3428	mΩ
	On-state slope resistance – High level	2000A to 7200A at T <sub>case</sub> = 125°C		-	0.2414	mΩ
t <sub>gd</sub>	Delay time	V <sub>D</sub> = 67% V <sub>DRM</sub> , gate source 30V, 10Ω t <sub>r</sub> = 0.5μs, T <sub>j</sub> = 25°C		-	3	μs
t <sub>q</sub>	Turn-off time	T <sub>j</sub> = 125°C, V <sub>R</sub> = 200V, dI/dt = 1A/μs, dV <sub>DR</sub> /dt = 20V/μs linear		-	600	μs
Q <sub>S</sub>	Stored charge	I <sub>T</sub> = 2000A, T <sub>j</sub> = 125°C, dI/dt – 1A/μs,		2000	4750	μC
I <sub>L</sub>	Latching current	T <sub>j</sub> = 25°C, V <sub>D</sub> = 5V		-	3	A
I <sub>H</sub>	Holding current	T <sub>j</sub> = 25°C, R <sub>G-K</sub> = ∞, I <sub>TM</sub> = 500A, I <sub>T</sub> = 5A		-	300	mA

## GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% $V_{DRM}, T_{case} = 125^{\circ}C$	0.4	V
$I_{GT}$	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	350	mA
$I_{GD}$	Gate non-trigger current	At 50% $V_{DRM}, T_{case} = 125^{\circ}C$	15	mA

## CURVES

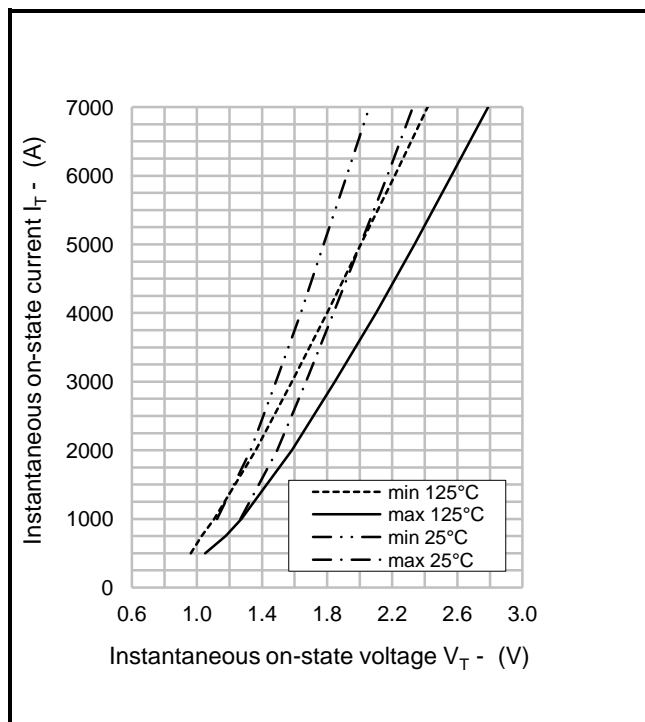


Fig.2 Maximum & minimum on-state characteristics

### $V_{TM}$ EQUATION

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

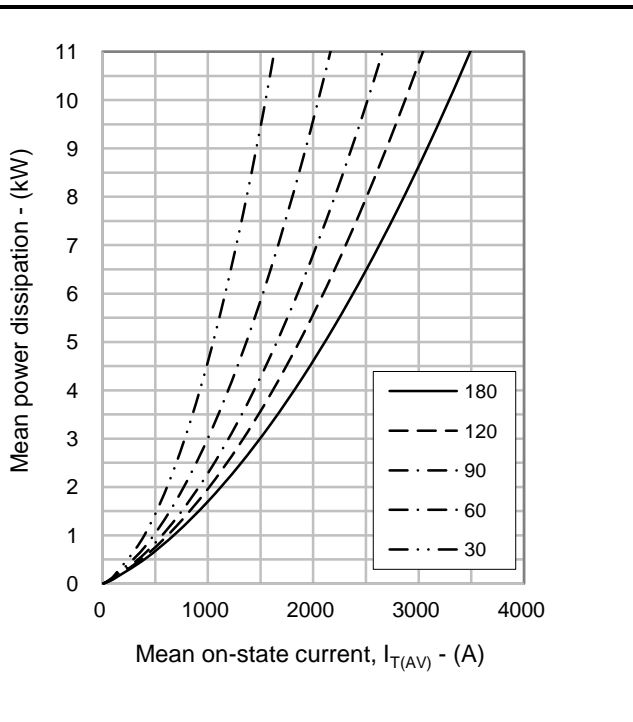
Where  $A = -0.450546$

$B = 0.251217$

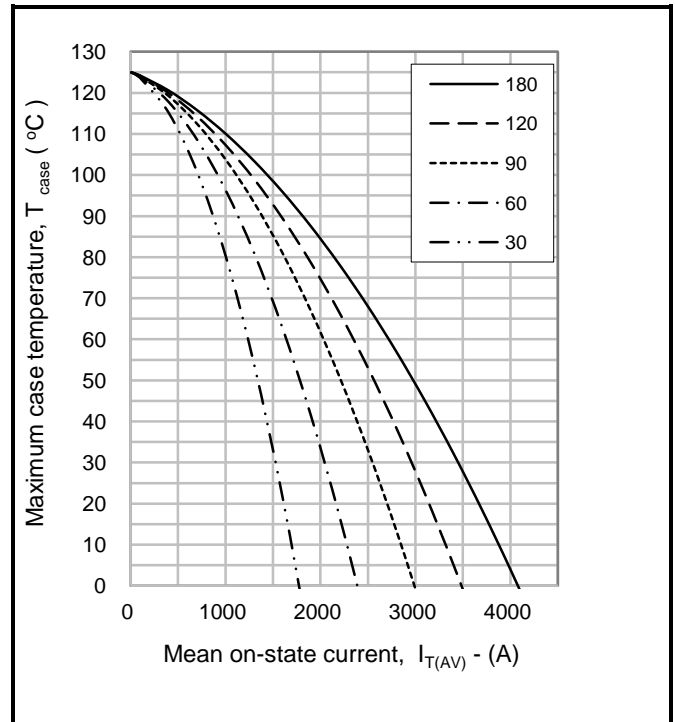
$C = 0.000242$

$D = -0.008134$

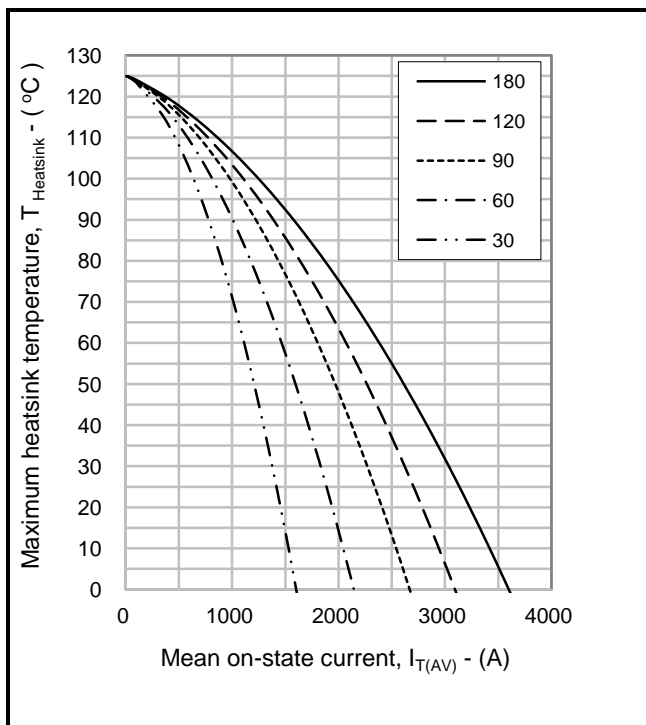
these values are valid for  $T_j = 125^{\circ}C$  for  $I_T$  500A to 7200A



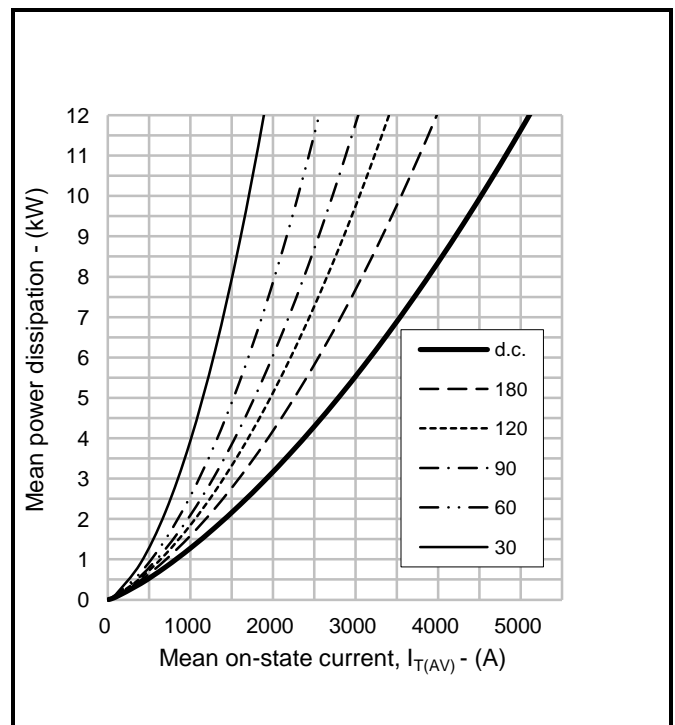
**Fig.3 On-state power dissipation – sine wave**



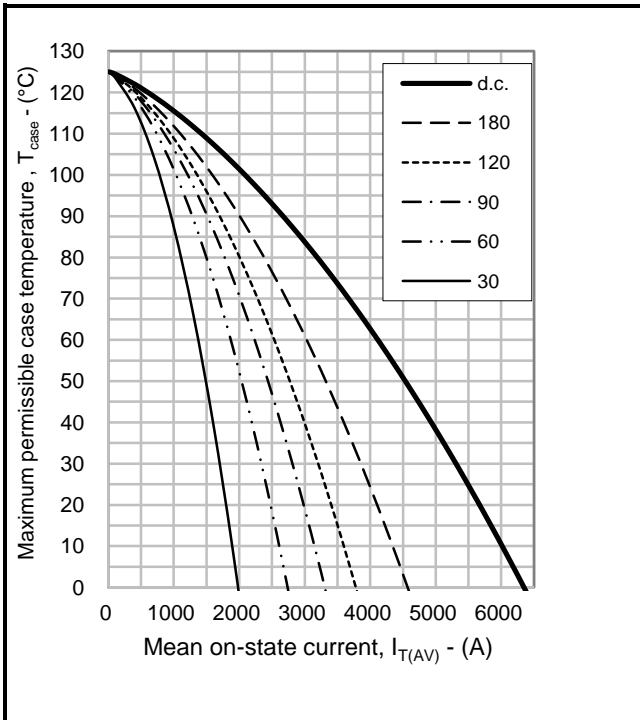
**Fig.4 Maximum permissible case temperature, double side cooled – sine wave**



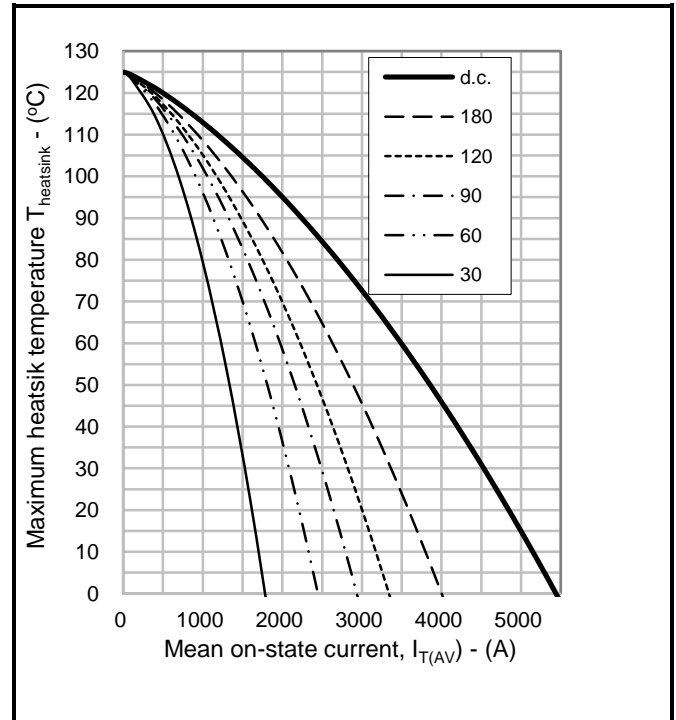
**Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave**



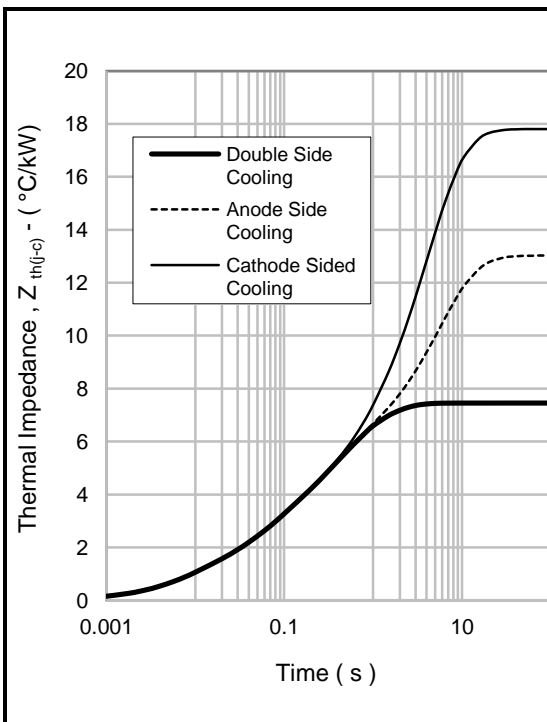
**Fig.6 On-state power dissipation – rectangular wave**



**Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave**



**Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave**



**Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)**

		1	2	3	4
Double side cooled	$R_{\theta}$ (°C/kW)	0.9206	1.8299	3.4022	1.3044
	$T_{\theta}$ (s)	0.0076807	0.0579454	0.4078613	1.2085
Anode side cooled	$R_{\theta}$ (°C/kW)	0.9032	1.6719	3.0101	7.4269
	$T_{\theta}$ (s)	0.0075871	0.0536531	0.3144537	5.624
Cathode side cooled	$R_{\theta}$ (°C/kW)	0.9478	2.0661	1.6884	13.0847
	$T_{\theta}$ (s)	0.0078442	0.0645541	0.3894389	4.1447

#### $\Delta R_{\theta(j-c)}$ Conduction

Tables show the increments of thermal resistance  $R_{\theta(j-c)}$  when the device operates at conduction angles other than d.c.

Double side cooling			Anode Side Cooling			Cathode Sided Cooling		
$\eta^\circ$	$\Delta Z_{\theta} (z)$		$\eta^\circ$	$\Delta Z_{\theta} (z)$		$\eta^\circ$	$\Delta Z_{\theta} (z)$	
	sine.	rect.		sine.	rect.		sine.	rect.
180	1.34	0.88	180	1.34	0.88	180	1.33	0.88
120	1.57	1.30	120	1.57	1.30	120	1.57	1.29
90	1.83	1.54	90	1.84	1.54	90	1.83	1.53
60	2.08	1.81	60	2.08	1.81	60	2.07	1.80
30	2.27	2.11	30	2.28	2.11	30	2.26	2.10
15	2.36	2.28	15	2.37	2.28	15	2.35	2.26

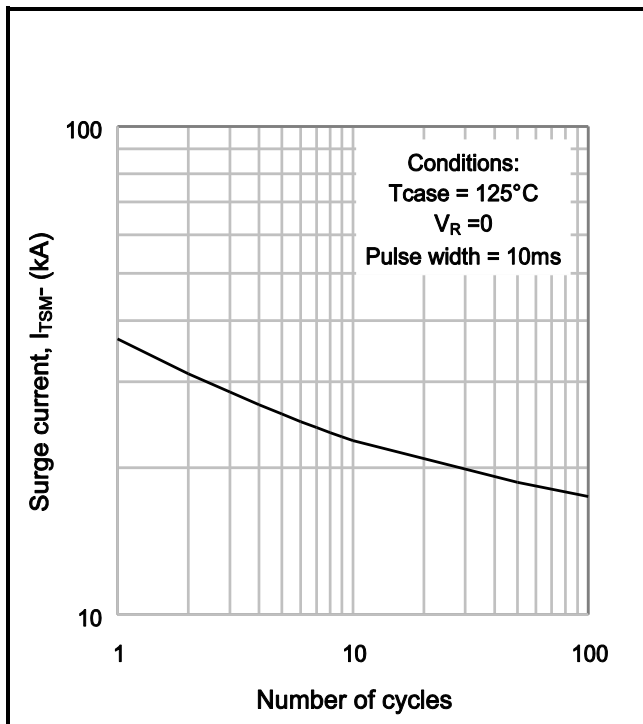


Fig.10 Multi-cycle surge current

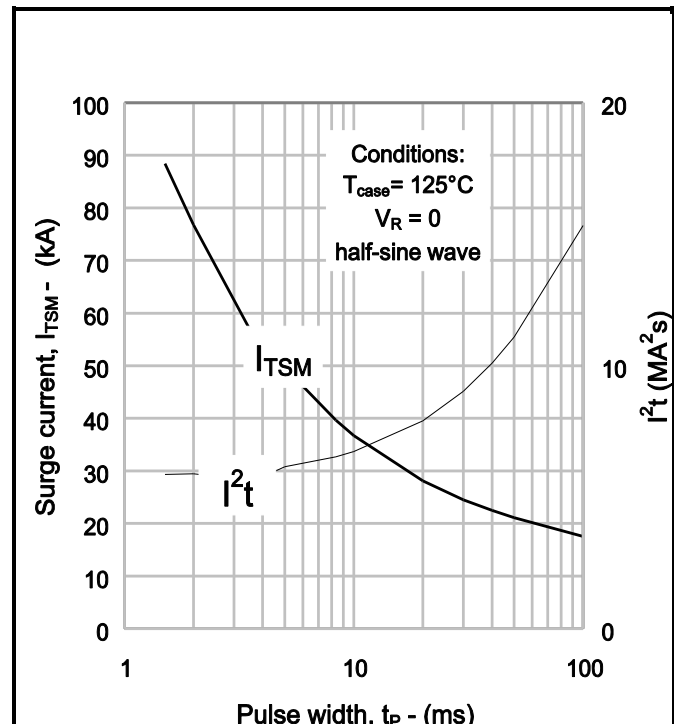


Fig.11 Single-cycle surge current

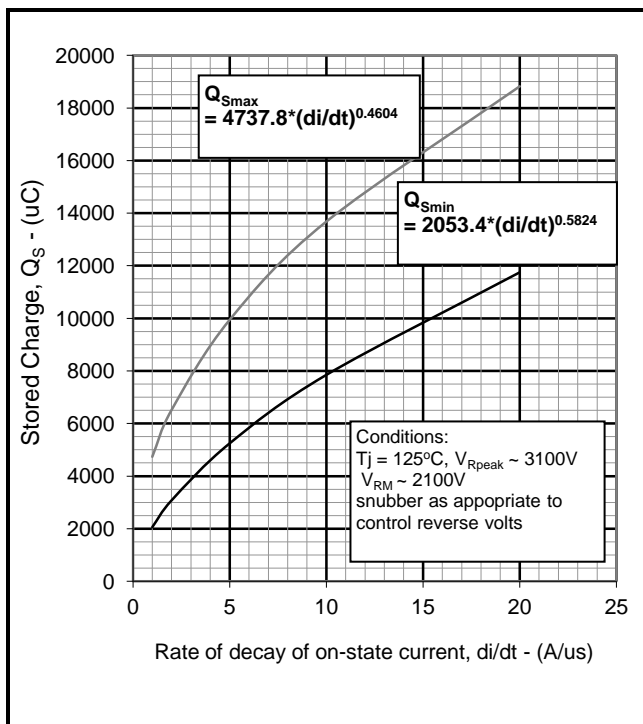


Fig.12 Stored charge

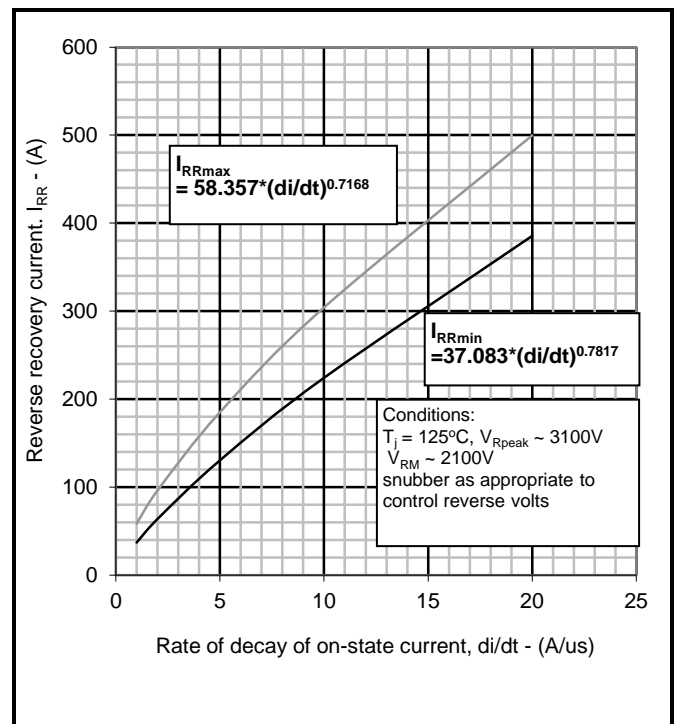


Fig.13 Reverse recovery current

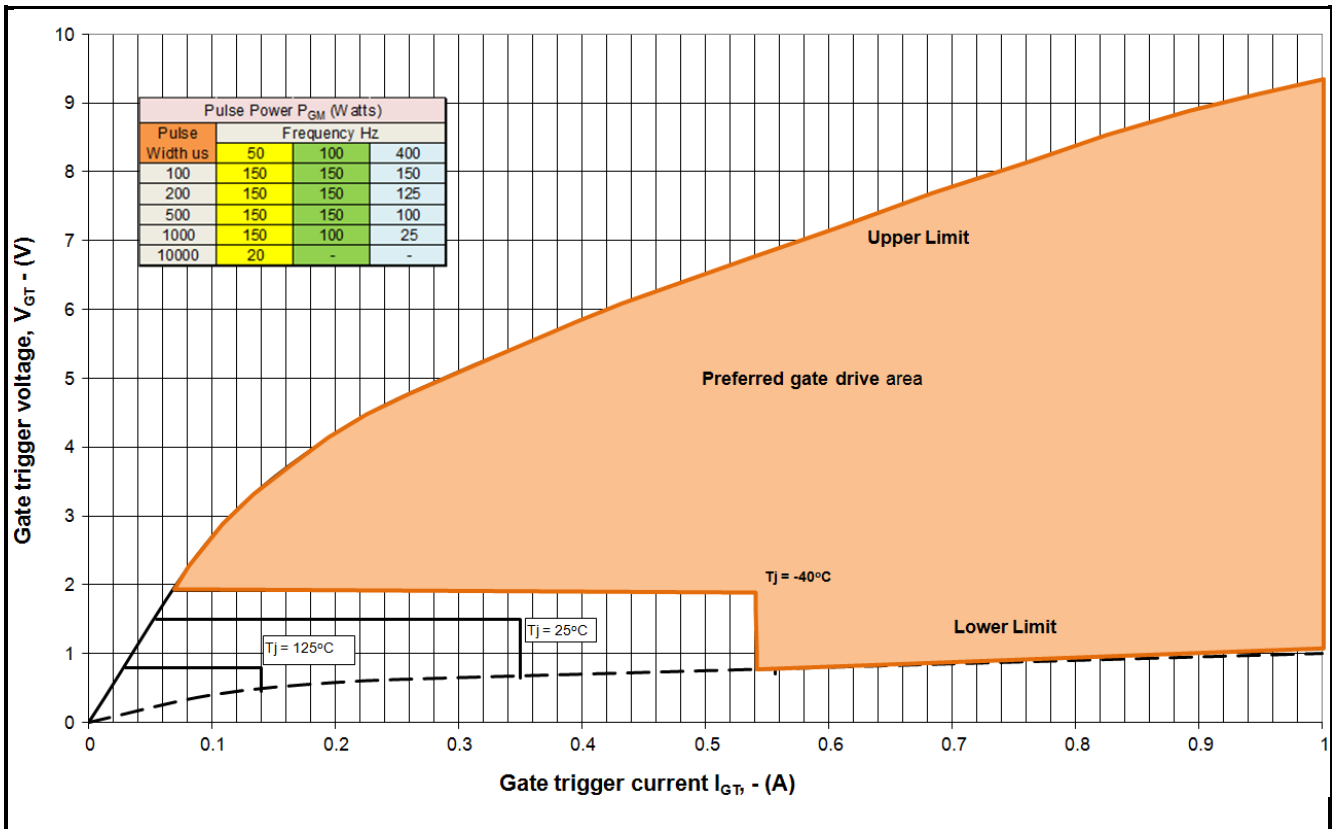


Fig14 Gate Characteristics

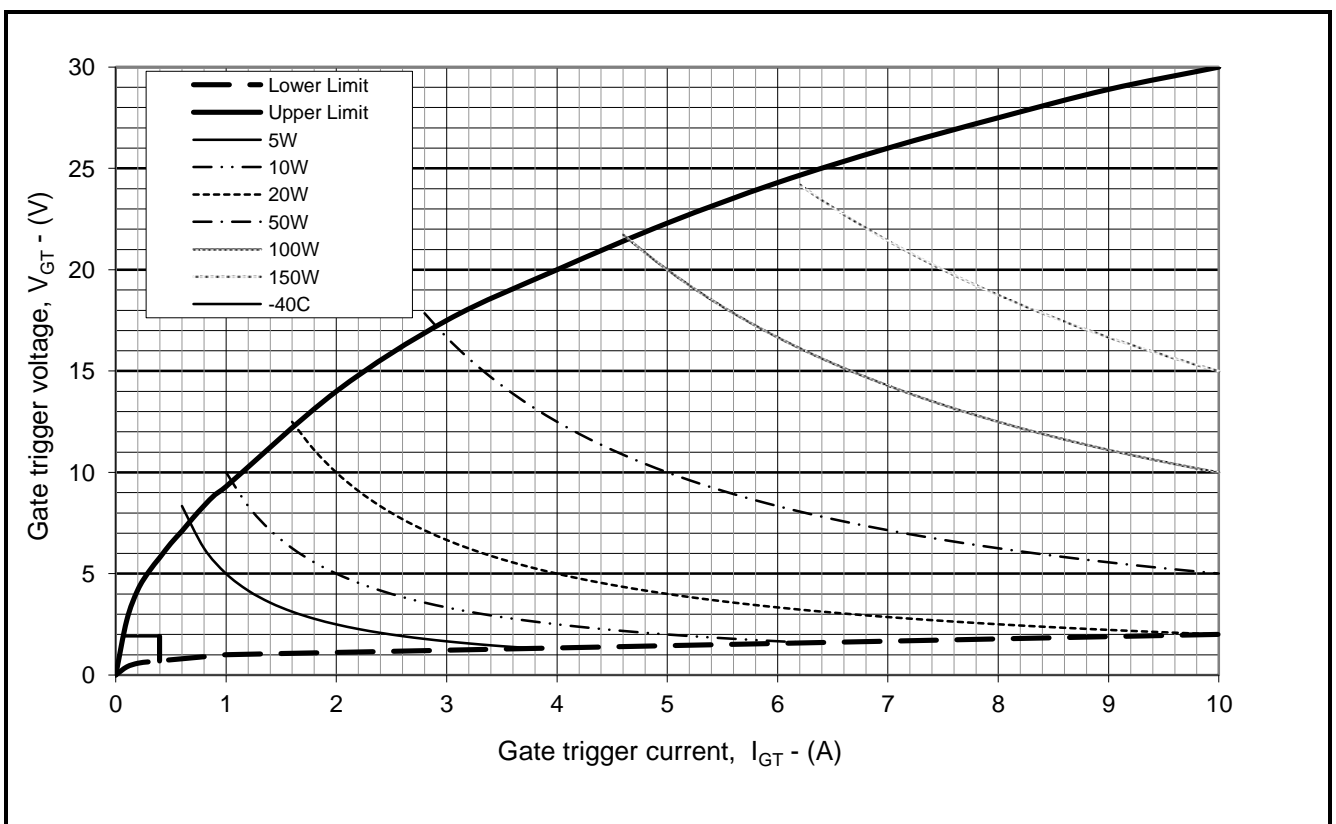


Fig. 15 Gate characteristics



## PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

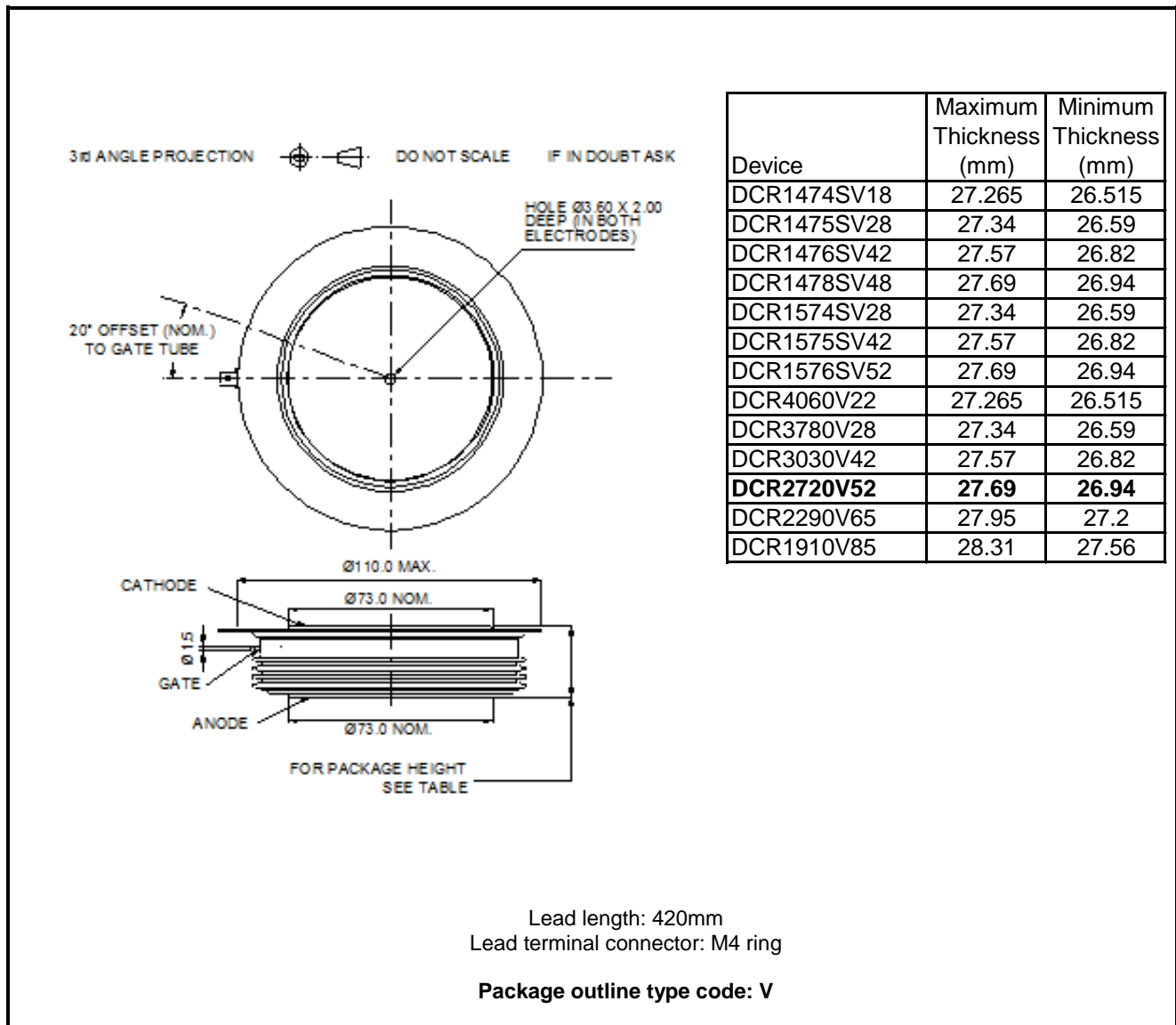


Fig.16 Package outline

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